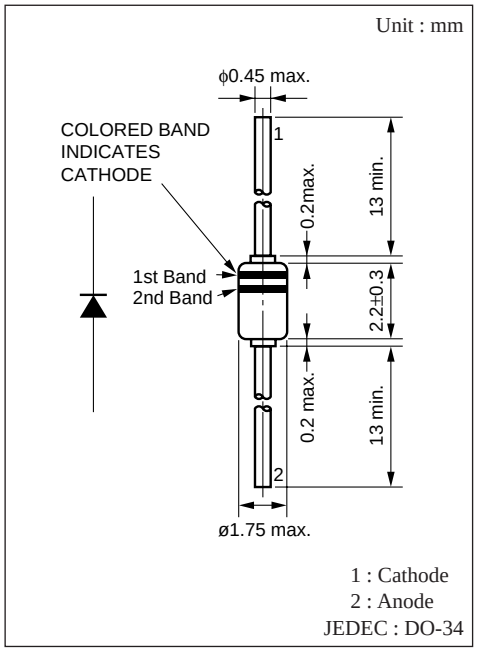
MA859

Silicon epitaxial planer type

For band switching



■ Features

- Extra-small DHD envelope, enabling 5mm pitch insertion
- Less voltage dependence of the capacity C_t between pins
- Low forward dynamic resistance r_f
- Optimum for a band switching of tuner

■ Absolute Maximum Ratings (Ta= 25˚C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	35	V
Forward current (DC)	I_F	100	mA
Operating ambient temperature	T_{opr}	– 25 to + 85	˚C
Storage temperature	T_{stg}	– 55 to +100	˚C

■ Electrical Characteristics (Ta= 25˚C)

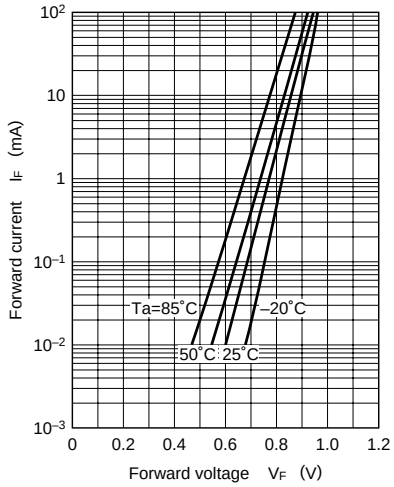
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R * 1	V_R= 33V			100	nA
Forward voltage (DC)	V_F	I_F=100mA			1.1	V
Terminal capacitance	C_t	V_R= 6V, f=1MHz		0.8	1.2	pF
Forward dynamic resistance	r_f * 2	I_F= 2mA, f=100MHz		0.5	0.65	Ω
	r_f * 3			0.77	0.98	Ω

Note 1 : Rated input/output frequency : 100MHz
2 : * 1 Measurement with the beam shielded
* 2 r_f measurement device : Nihon Koshuha MODEL TDC-121 A Lead length 5mm
* 3 r_f measurement device : YHP 4191A Lead length 5mm

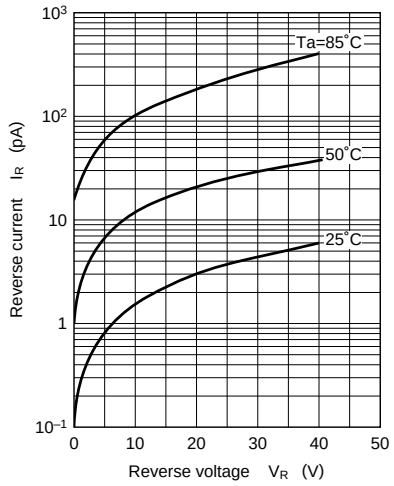
■ Cathode Indication

Type No.		MA859
Color	1st Band	Black
	2nd Band	Blue

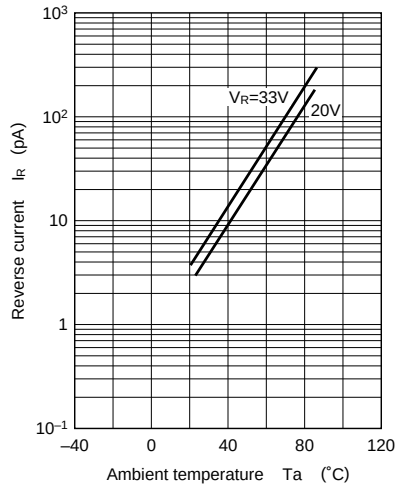
$I_F - V_F$



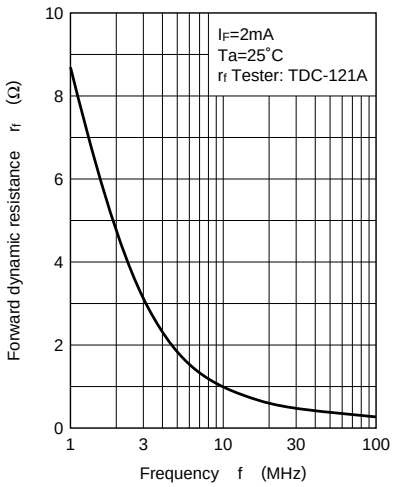
$I_R - V_R$



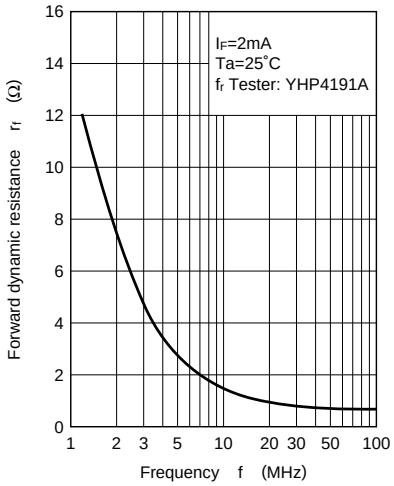
$I_R - Ta$



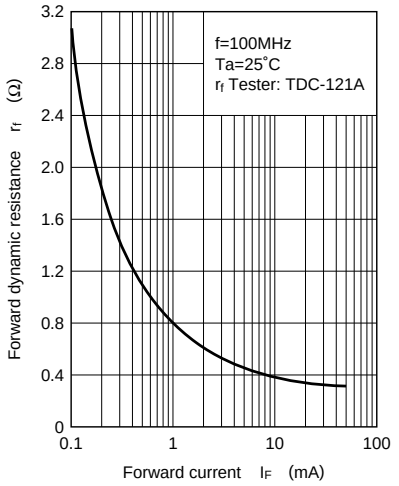
$r_f - f$



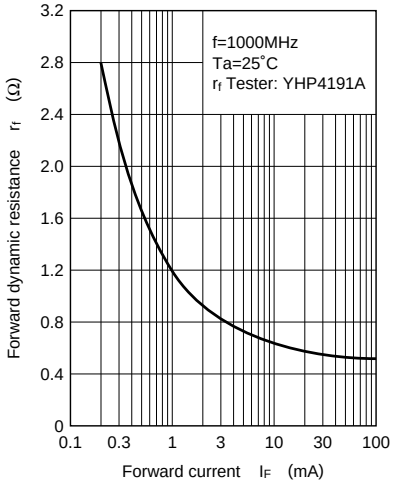
$r_f - f$



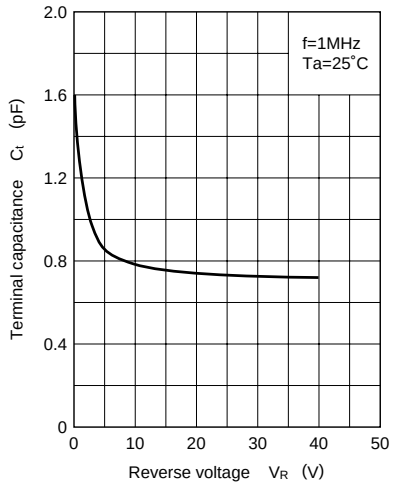
$r_f - I_F$



$r_f - I_F$



$C_D - V_R$



$I_{F(surge)} - t_W$